NSN 5961-01-135-0719

Diode Semiconductor Device - Page 1 of 1

View Online at https://aerobasegroup.com/nsn/5961-01-135-0719

Inclosure Material:

Metal

Overall Length:

0.405 inches

Mounting Facility Quantity:

1

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

Do-4

Electrode Internally-electrically Connected To Case:

Cathode

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

0.437 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

500.0 reverse voltage, peak and 350.0 reverse voltage, total rms

Current Rating Per Characteristic:

12.00 amperes forward current, average absolute

Power Rating Per Characteristic:

3.0 milliwatts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

190.0 degrees celsius junction

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 tab, solder lug and 1 threaded stud

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0